

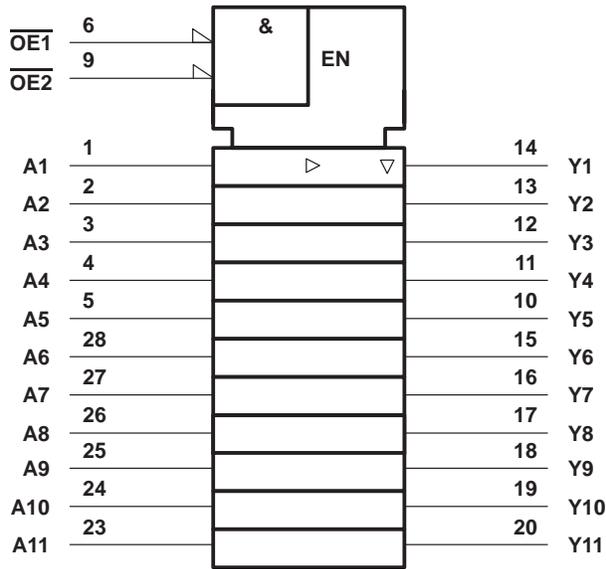
SN74BCT2410

11-BIT MOS MEMORY DRIVER

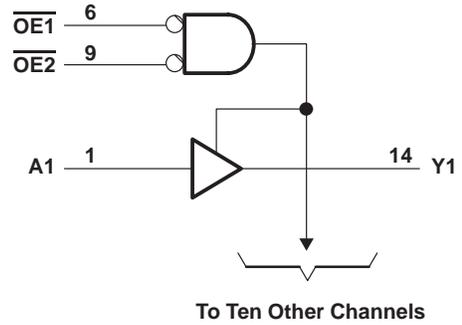
WITH 3-STATE OUTPUTS

SCBS119B – JUNE 1990 – REVISED NOVEMBER 1993

logic symbol†

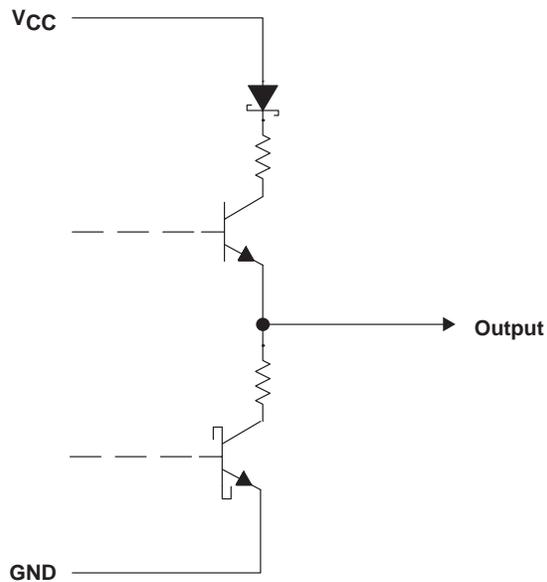


logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

schematic of each output



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	-0.5 V to 7 V
Input voltage range, V_I (see Note 1)	-0.5 V to 7 V
Voltage range applied to any output in the disabled or power-off state, V_O	-0.5 V to 5.5 V
Voltage range applied to any output in the high state, V_O	-0.5 V to V_{CC}
Input clamp current, I_{IK} ($V_I < 0$)	-30 mA
Current into any output in the low state, I_O	60 mA
Operating free-air temperature range	0°C to 70°C
Storage temperature range	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability

NOTE 1: The input negative-voltage rating may be exceeded if the input clamp-current rating is observed.

recommended operating conditions (see Note 2)

	MIN	NOM	MAX	UNIT
V_{CC} Supply voltage	4.5	5	5.5	V
V_{IH} High-level input voltage	2			V
V_{IL} Low-level input voltage			0.8	V
I_{IK} Input clamp current			-18	mA
I_{OH} High-level output current			-12	mA
I_{OL} Low-level output current			12	mA
T_A Operating free-air temperature	0		70	°C

NOTE 2: Unused or floating inputs must be held high or low.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
V_{IK}	$V_{CC} = 4.5$ V, $I_I = -18$ mA			-1.2	V
V_{OH}	$V_{CC} = 4.5$ V	$I_{OH} = -3$ mA	2.5	3.5	V
		$I_{OH} = -12$ mA	2	3.1	
V_{OL}	$V_{CC} = 4.5$ V, $I_{OL} = 12$ mA		0.42	0.8	V
I_I	$V_{CC} = 5.5$ V, $V_I = 5.5$ V			0.1	mA
I_{IH}	$V_{CC} = 5.5$ V, $V_I = 2.7$ V			20	μA
I_{IL}	$V_{CC} = 5.5$ V, $V_I = 0.5$ V			-0.1	mA
I_{OZH}	$V_{CC} = 5.5$ V, $V_O = 2.7$ V			50	μA
I_{OZL}	$V_{CC} = 5.5$ V, $V_O = 0.5$ V			-50	μA
I_{O}^{\S}	$V_{CC} = 5.5$ V, $V_O = 2.25$ V	-15		-70	mA
I_{CCL}	$V_{CC} = 5.5$ V, $V_O = 0$			40	mA
I_{CCH}	$V_{CC} = 5.5$ V, $V_O = 0$			40	mA
I_{CCZ}	$V_{CC} = 5.5$ V, $V_O = 0$			6.5	mA
C_i	$V_{CC} = 5$ V, $V_I = 2.5$ V or 0.5 V		6		pF
C_o	$V_{CC} = 5$ V, $V_O = 2.5$ V or 0.5 V		10		pF

‡ All typical values are at $V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$.

§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.



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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50$ pF (unless otherwise noted) (see Note 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 5$ V, $T_A = 25^\circ$ C			MIN	MAX	UNIT
			MIN	TYP	MAX			
t_{PLH}	A	Y	2	4.9	6.5	2	8.5	ns
t_{PHL}			2.3	5.6	7.5	2.3	8.5	
t_{PZH}	\overline{OE}	Y	4.5	10.3	13	4.5	16.5	ns
t_{PZL}			2	11.4	16	2	19	
t_{PHZ}	\overline{OE}	Y	3.4	7	9.5	3.4	12	ns
t_{PLZ}			5.3	9.2	11.5	5.3	13.5	

NOTE 3: Load circuits and voltage waveforms are shown in Section 1.

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